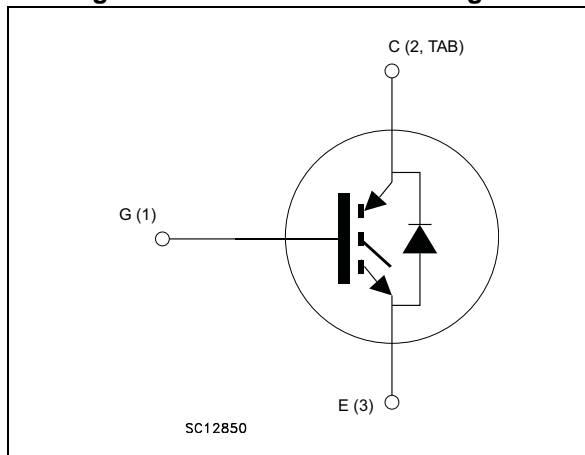


Figure 1. Internal schematic diagram



## Features

- Maximum junction temperature:  $T_J = 175\text{ °C}$
- Very high speed switching series
- Tail-less switching off
- Low saturation voltage:  $V_{CE(sat)} = 1.85\text{ V (typ.)}$  @  $I_C = 30\text{ A}$
- Tight parameters distribution
- Safe paralleling
- Low thermal resistance
- Very fast soft recovery antiparallel diode
- Lead free package

## Applications

- Photovoltaic inverters
- Uninterruptible power supply
- Welding
- Power factor correction
- Very high frequency converters

## Description

This device is an IGBT developed using an advanced proprietary trench gate and field stop structure. The device is part of the "V" series of IGBTs, which represent an optimum compromise between conduction and switching losses to maximize the efficiency of very high frequency converters. Furthermore, a positive  $V_{CE(sat)}$  temperature coefficient and very tight parameter distribution result in safer paralleling operation.

Table 1. Device summary

| Order codes  | Marking    | Package            | Packaging     |
|--------------|------------|--------------------|---------------|
| STGB30V60DF  | GB30V60DF  | D <sup>2</sup> PAK | Tape and reel |
| STGP30V60DF  | GP30V60DF  | TO-220             | Tube          |
| STGW30V60DF  | GW30V60DF  | TO-247             | Tube          |
| STGWT30V60DF | GWT30V60DF | TO-3P              | Tube          |

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

| Symbol         | Parameter   | Value       | Unit |
|----------------|---|-------------|------|
| $V_{CES}$      | Collector-emitter voltage ( $V_{GE} = 0$ )            | 600         | V    |
| $I_C$          | Continuous collector current at $T_C = 25\text{ °C}$  | 60          | A    |
| $I_C$          | Continuous collector current at $T_C = 100\text{ °C}$ | 30          | A    |
| $I_{CP}^{(1)}$ | Pulsed collector current                              | 120         | A    |
| $V_{GE}$       | Gate-emitter voltage                                  | $\pm 20$    | V    |
| $I_F$          | Continuous forward current at $T_C = 25\text{ °C}$    | 60          | A    |
| $I_F$          | Continuous forward current at $T_C = 100\text{ °C}$   | 30          | A    |
| $I_{FP}^{(1)}$ | Pulsed forward current                                | 120         | A    |
| $P_{TOT}$      | Total dissipation at $T_C = 25\text{ °C}$             | 258         | W    |
| $T_{STG}$      | Storage temperature range                             | - 55 to 150 | °C   |
| $T_J$          | Operating junction temperature                        | - 55 to 175 | °C   |

1. Pulse width limited by maximum junction temperature and turn-off within RBSOA

**Table 3. Thermal data**

| Symbol     | Parameter                              | Value | Unit |
|------------|--|-------|------|
| $R_{thJC}$ | Thermal resistance junction-case IGBT  | 0.58  | °C/W |
| $R_{thJC}$ | Thermal resistance junction-case diode | 2.08  | °C/W |
| $R_{thJA}$ | Thermal resistance junction-ambient    | 50    | °C/W |

## 2 Electrical characteristics

$T_J = 25\text{ °C}$  unless otherwise specified.

**Table 4. Static characteristics**

| Symbol        | Parameter  | Test conditions  | Min. | Typ. | Max. | Unit          |
|---------------|--|--|------|------|------|---------------|
| $V_{(BR)CES}$ | Collector-emitter breakdown voltage ( $V_{GE} = 0$ ) | $I_C = 2\text{ mA}$  | 600  |      |      | V             |
| $V_{CE(sat)}$ | Collector-emitter saturation voltage                 | $V_{GE} = 15\text{ V}, I_C = 30\text{ A}$                          |      | 1.85 | 2.3  | V             |
|               |  | $V_{GE} = 15\text{ V}, I_C = 30\text{ A}$<br>$T_J = 125\text{ °C}$ |      | 2.15 |      |               |
|               |  | $V_{GE} = 15\text{ V}, I_C = 30\text{ A}$<br>$T_J = 175\text{ °C}$ |      | 2.35 |      |               |
| $V_F$         | Forward on-voltage                                   | $I_F = 30\text{ A}$  |      | 2    | 2.6  | V             |
|               |  | $I_F = 30\text{ A}, T_J = 125\text{ °C}$                           |      | 1.7  |      | V             |
|               |  | $I_F = 30\text{ A}, T_J = 175\text{ °C}$                           |      | 1.6  |      | V             |
| $V_{GE(th)}$  | Gate threshold voltage                               | $V_{CE} = V_{GE}, I_C = 1\text{ mA}$                               | 5    | 6    | 7    | V             |
| $I_{CES}$     | Collector cut-off current ( $V_{GE} = 0$ )           | $V_{CE} = 600\text{ V}$  |      |      | 25   | $\mu\text{A}$ |
| $I_{GES}$     | Gate-emitter leakage current ( $V_{CE} = 0$ )        | $V_{GE} = \pm 20\text{ V}$   |      |      | 250  | nA            |

**Table 5. Dynamic characteristics**

| Symbol    | Parameter                    | Test conditions  | Min. | Typ. | Max. | Unit |
|-----------|------------------------------|--|------|------|------|------|
| $C_{ies}$ | Input capacitance            | $V_{CE} = 25\text{ V}, f = 1\text{ MHz},$<br>$V_{GE} = 0$  | -    | 3750 | -    | pF   |
| $C_{oes}$ | Output capacitance           |  | -    | 120  | -    | pF   |
| $C_{res}$ | Reverse transfer capacitance |  | -    | 77   | -    | pF   |
| $Q_g$     | Total gate charge            | $V_{CC} = 480\text{ V}, I_C = 30\text{ A},$<br>$V_{GE} = 15\text{ V},$ see <a href="#">Figure 29</a> | -    | 163  | -    | nC   |
| $Q_{ge}$  | Gate-emitter charge          |  | -    | 28   | -    | nC   |
| $Q_{gc}$  | Gate-collector charge        |  | -    | 72   | -    | nC   |

Table 6. IGBT switching characteristics (inductive load)

| Symbol          | Parameter                 | Test conditions   | Min. | Typ. | Max.    | Unit       |
|-----------------|---------------------------|---|------|------|---------|------------|
| $t_{d(on)}$     | Turn-on delay time        | $V_{CE} = 400\text{ V}$ , $I_C = 30\text{ A}$ ,<br>$R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ ,<br>see <a href="#">Figure 28</a>                                     | -    | 45   | -       | ns         |
| $t_r$           | Current rise time         |   | -    | 16   | -       | ns         |
| $(di/dt)_{on}$  | Turn-on current slope     |   | -    | 1500 | -       | A/ $\mu$ s |
| $t_{d(off)}$    | Turn-off delay time       |   | -    | 189  | -       | ns         |
| $t_f$           | Current fall time         |   | -    | 19   | -       | ns         |
| $E_{on}^{(1)}$  | Turn-on switching losses  |   | -    | 383  | -       | $\mu$ J    |
| $E_{off}^{(2)}$ | Turn-off switching losses |   | -    | 233  | -       | $\mu$ J    |
| $E_{ts}$        | Total switching losses    | -   | 616  | -    | $\mu$ J |            |
| $t_{d(on)}$     | Turn-on delay time        | $V_{CE} = 400\text{ V}$ , $I_C = 30\text{ A}$ ,<br>$R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ ,<br>$T_J = 175\text{ }^\circ\text{C}$ , see <a href="#">Figure 28</a> | -    | 42   | -       | ns         |
| $t_r$           | Current rise time         |   | -    | 17   | -       | ns         |
| $(di/dt)_{on}$  | Turn-on current slope     |   | -    | 1337 | -       | A/ $\mu$ s |
| $t_{d(off)}$    | Turn-off delay time       |   | -    | 193  | -       | ns         |
| $t_f$           | Current fall time         |   | -    | 32   | -       | ns         |
| $E_{on}^{(1)}$  | Turn-on switching losses  |   | -    | 794  | -       | $\mu$ J    |
| $E_{off}^{(2)}$ | Turn-off switching losses |   | -    | 378  | -       | $\mu$ J    |
| $E_{ts}$        | Total switching losses    | -   | 1172 | -    | $\mu$ J |            |

1. Energy losses include reverse recovery of the diode.
2. Turn-off losses include also the tail of the collector current.

Table 7. Diode switching characteristics (inductive load)

| Symbol       | Parameter  | Test conditions   | Min. | Typ. | Max. | Unit       |
|--------------|--|---|------|------|------|------------|
| $t_{rr}$     | Reverse recovery time                                      | $I_F = 30\text{ A}$ , $V_R = 400\text{ V}$ ,<br>$di/dt = 1000\text{ A}/\mu\text{s}$ ,<br>$V_{GE} = 15\text{ V}$ ,<br>(see <a href="#">Figure 28</a> )                                     | -    | 53   | -    | ns         |
| $Q_{rr}$     | Reverse recovery charge                                    |   | -    | 384  | -    | nC         |
| $I_{rrm}$    | Reverse recovery current                                   |   | -    | 14.5 | -    | A          |
| $dl_{rr}/dt$ | Peak rate of fall of reverse recovery current during $t_b$ |   | -    | 788  | -    | A/ $\mu$ s |
| $E_{rr}$     | Reverse recovery energy                                    |   | -    | 104  | -    | $\mu$ J    |
| $t_{rr}$     | Reverse recovery time                                      | $I_F = 30\text{ A}$ , $V_R = 400\text{ V}$ ,<br>$di/dt = 1000\text{ A}/\mu\text{s}$ ,<br>$V_{GE} = 15\text{ V}$ ,<br>$T_J = 175\text{ }^\circ\text{C}$ , (see <a href="#">Figure 28</a> ) | -    | 104  | -    | ns         |
| $Q_{rr}$     | Reverse recovery charge                                    |   | -    | 1352 | -    | nC         |
| $I_{rrm}$    | Reverse recovery current                                   |   | -    | 26   | -    | A          |
| $dl_{rr}/dt$ | Peak rate of fall of reverse recovery current during $t_b$ |   | -    | 310  | -    | A/ $\mu$ s |
| $E_{rr}$     | Reverse recovery energy                                    |   | -    | 407  | -    | $\mu$ J    |

## 2.1 Electrical characteristics (curves)

Figure 2. Power dissipation vs. case temperature

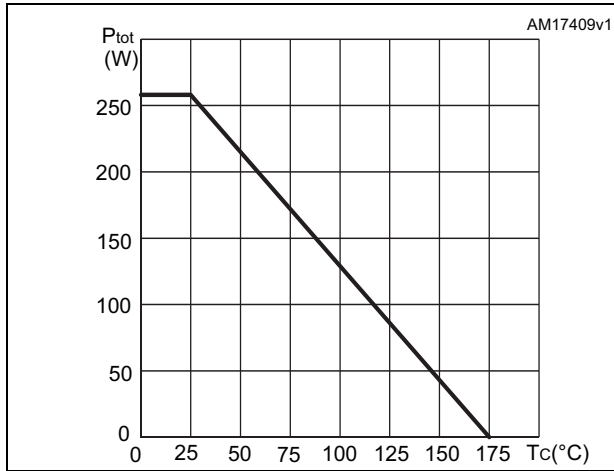


Figure 3. Collector current vs. case temperature

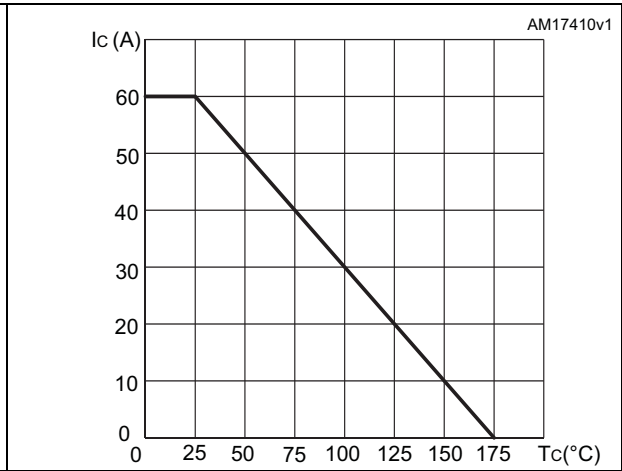


Figure 4. Output characteristics ( $T_J=25^\circ\text{C}$ )

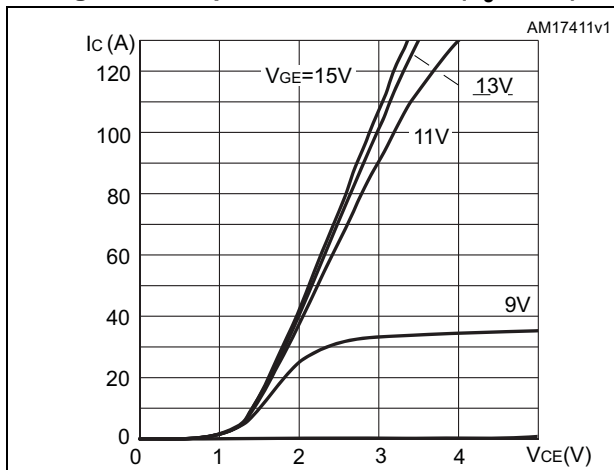


Figure 5. Output characteristics ( $T_J=175^\circ\text{C}$ )

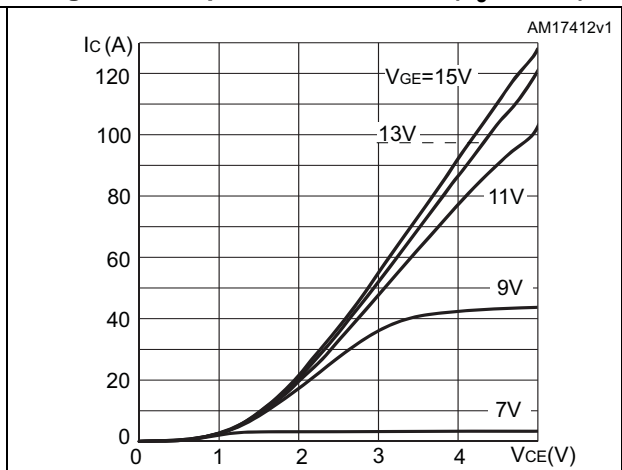


Figure 6.  $V_{CE(sat)}$  vs. junction temperature

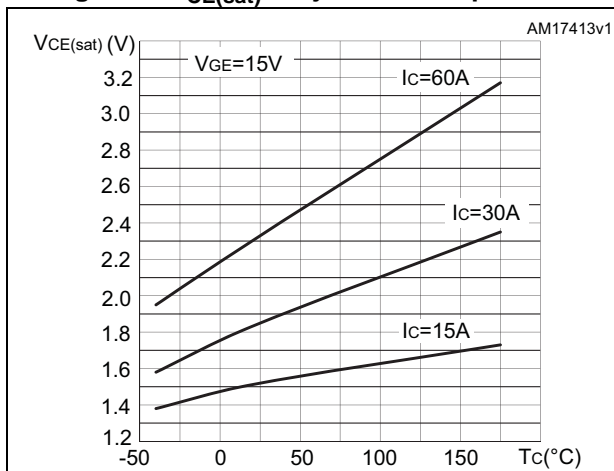


Figure 7.  $V_{CE(sat)}$  vs. collector current

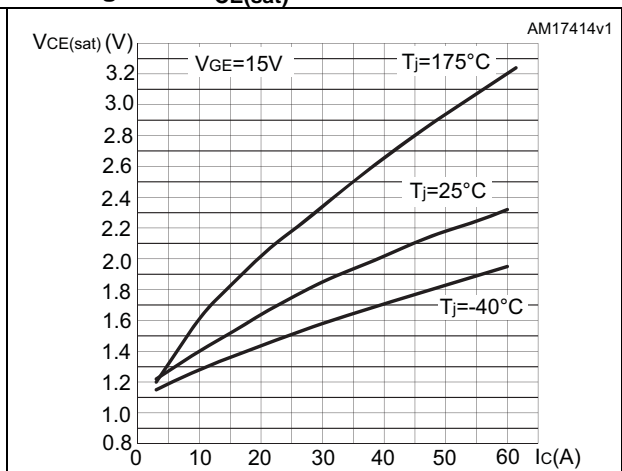


Figure 8. Collector current vs. switching frequency

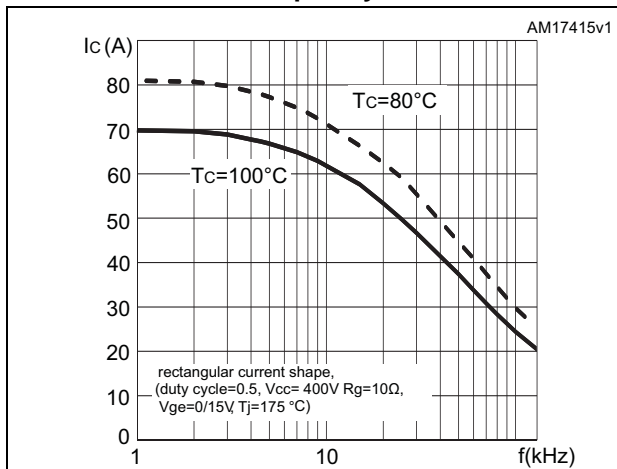


Figure 9. Forward bias safe operating area

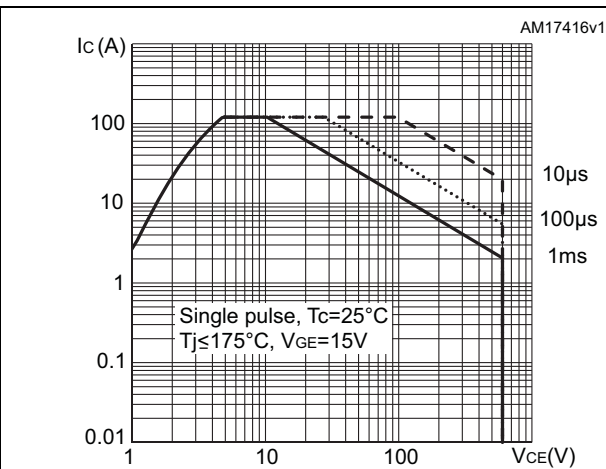


Figure 10. Transfer characteristics

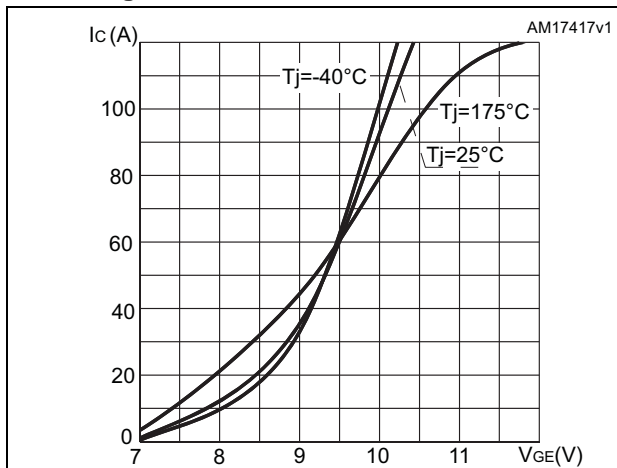


Figure 11. Diode V\_F vs. forward current

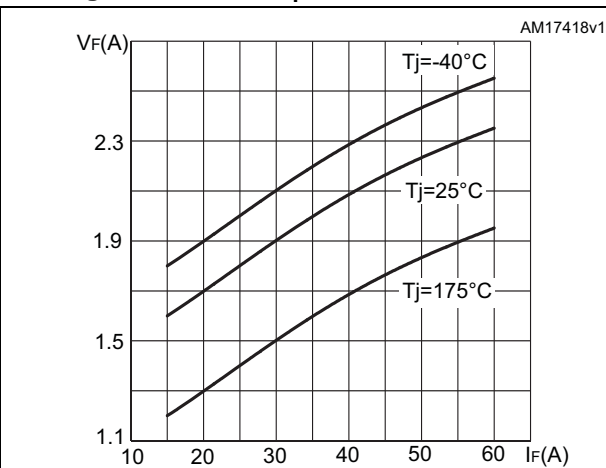


Figure 12. Normalized  $V_{GE(th)}$  vs junction temperature

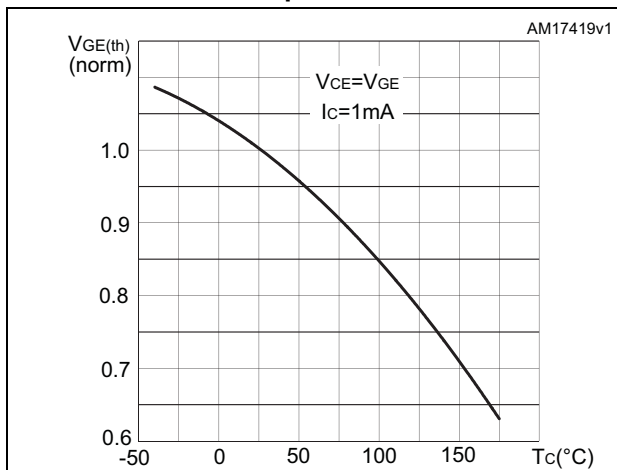


Figure 13. Normalized  $V_{(BR)CES}$  vs. junction temperature

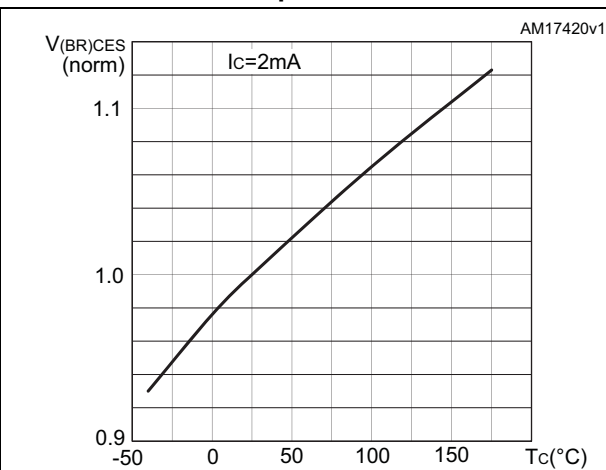


Figure 14. Capacitance variations

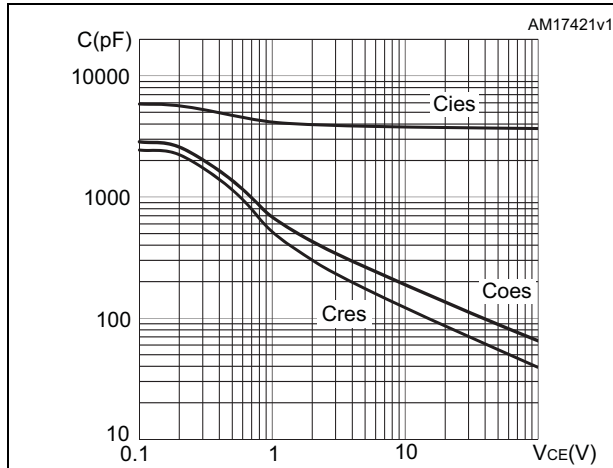


Figure 15. Gate charge vs. gate-emitter voltage

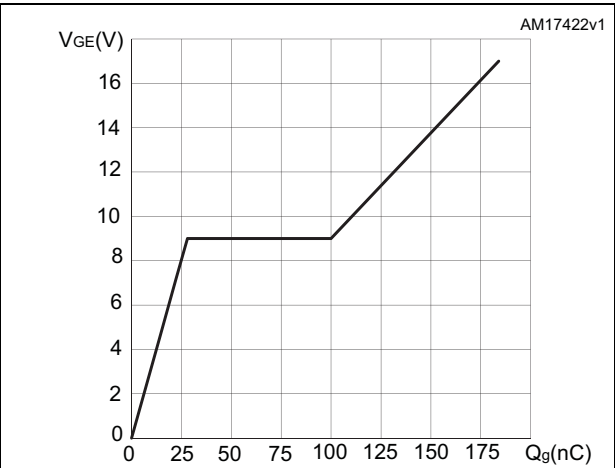


Figure 16. Switching losses vs. collector current

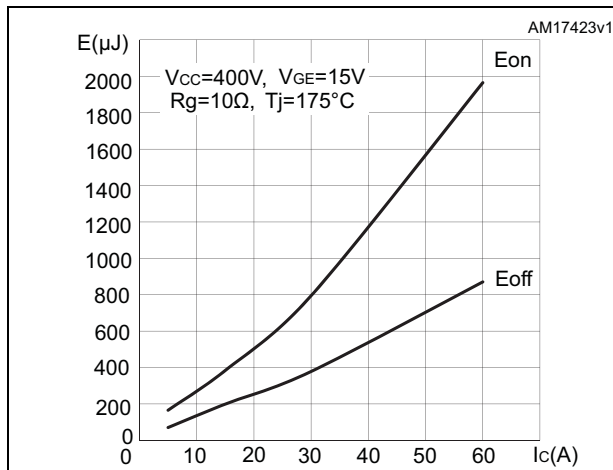


Figure 17. Switching losses vs. gate resistance

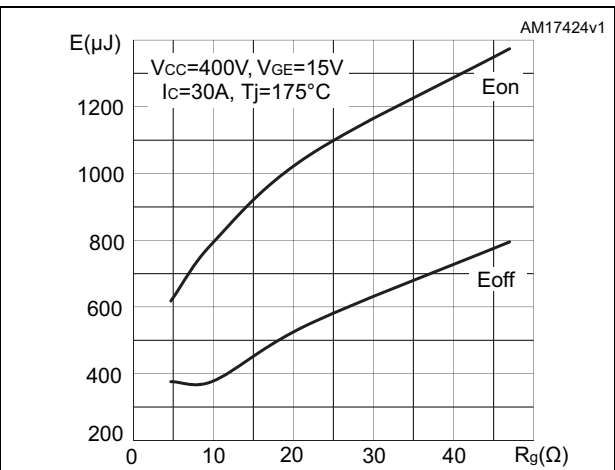


Figure 18. Switching losses vs. junction temperature

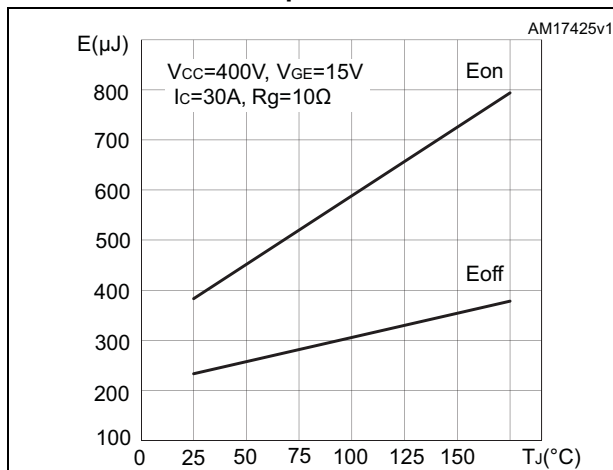


Figure 19. Switching losses vs. collector emitter voltage

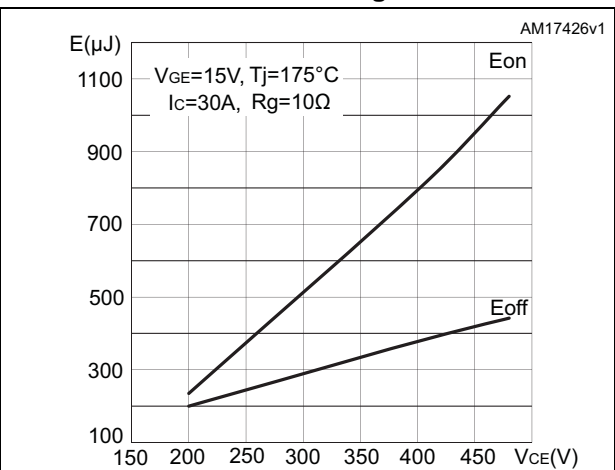


Figure 20. Switching times vs. collector current

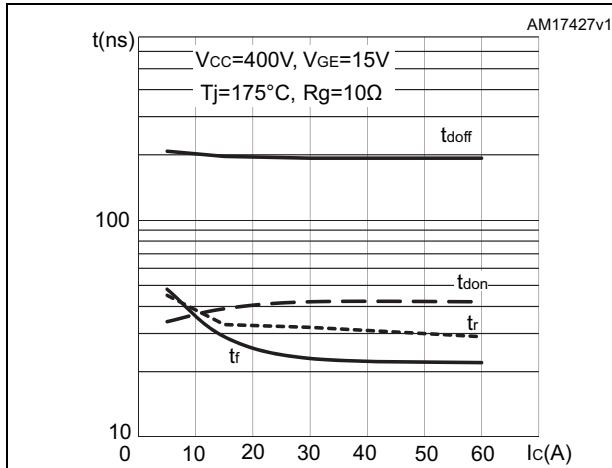


Figure 21. Switching times vs. gate resistance

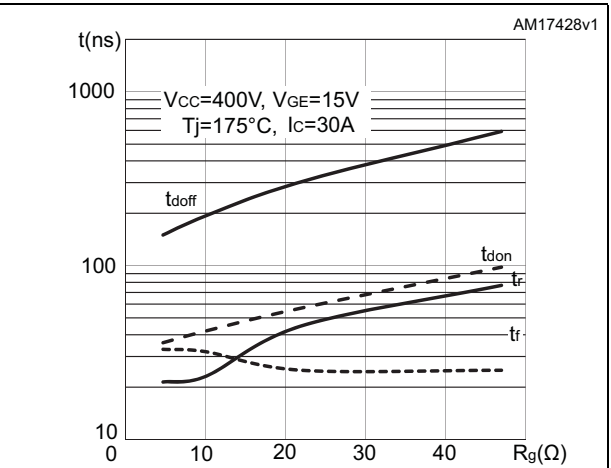


Figure 22. Reverse recovery current vs. diode current slope

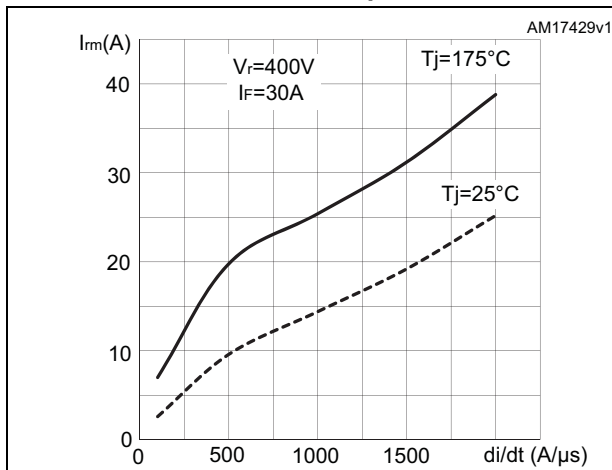


Figure 23. Reverse recovery time vs. diode current slope

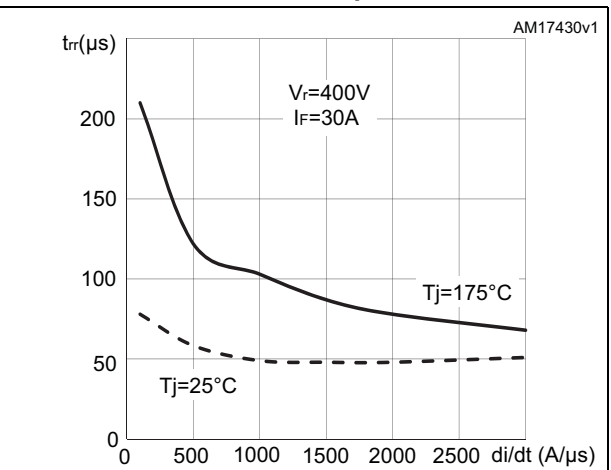


Figure 24. Reverse recovery charge vs. diode current slope

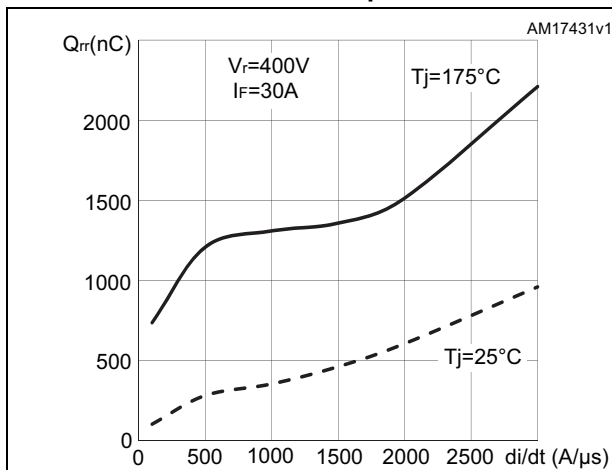


Figure 25. Reverse recovery energy vs. diode current slope

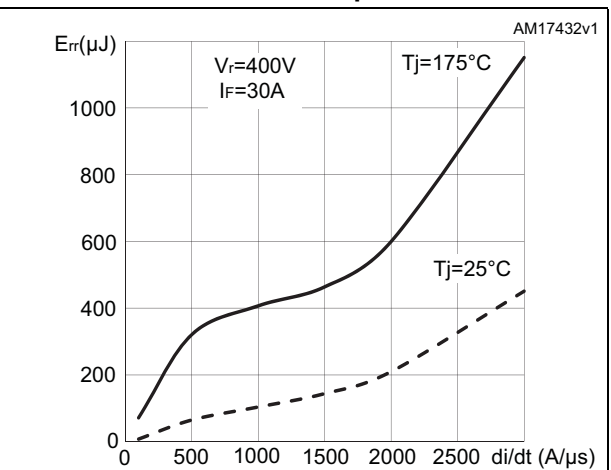




Figure 26. Thermal data for IGBT

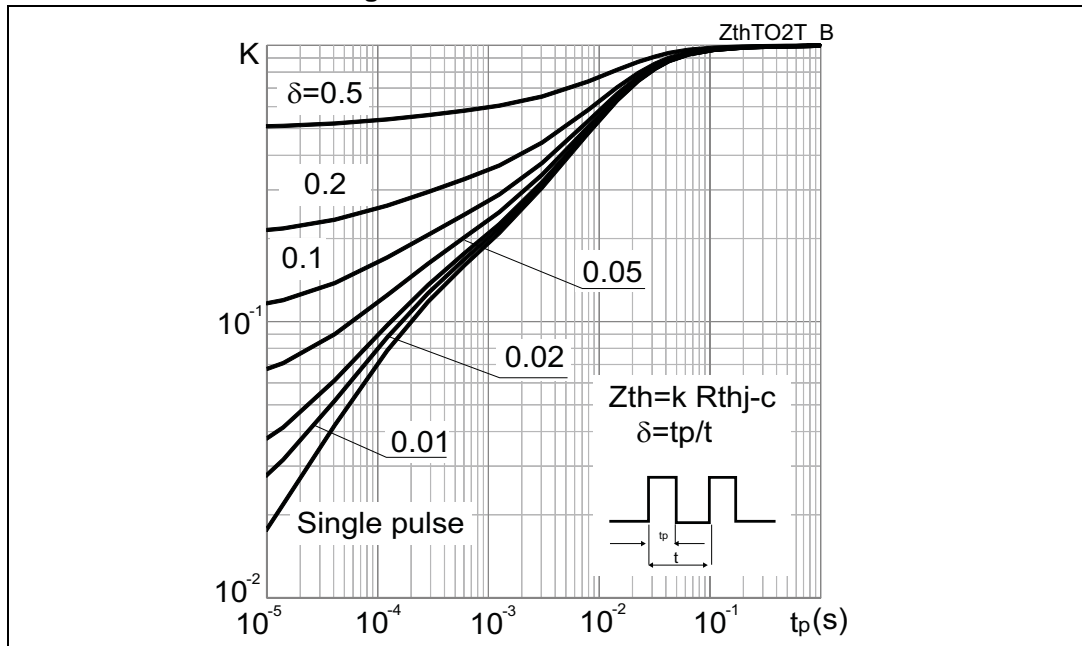
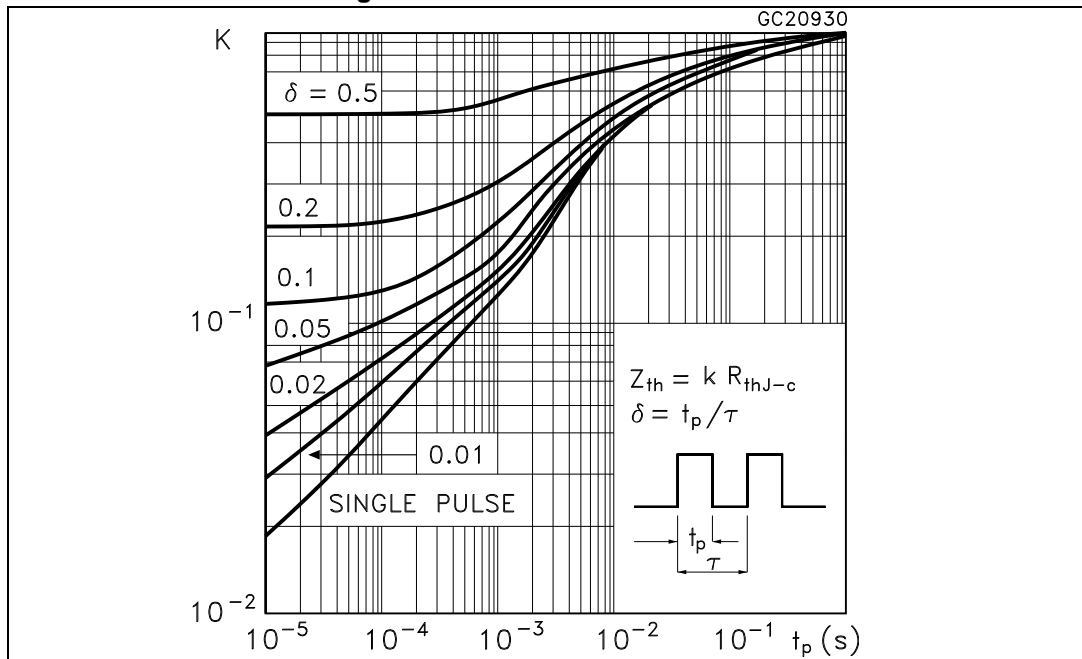


Figure 27. Thermal data for diode



### 3 Test circuits

Figure 28. Test circuit for inductive load switching

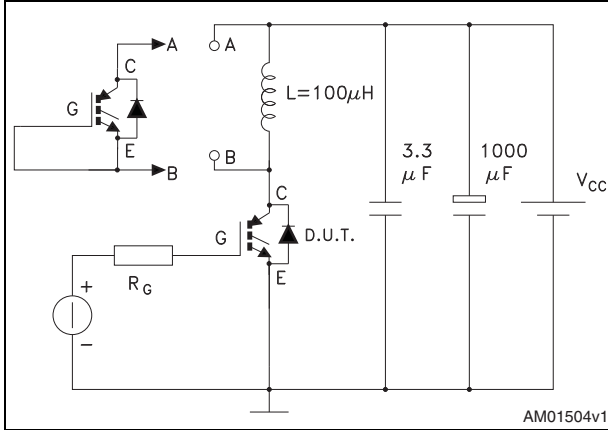


Figure 29. Gate charge test circuit

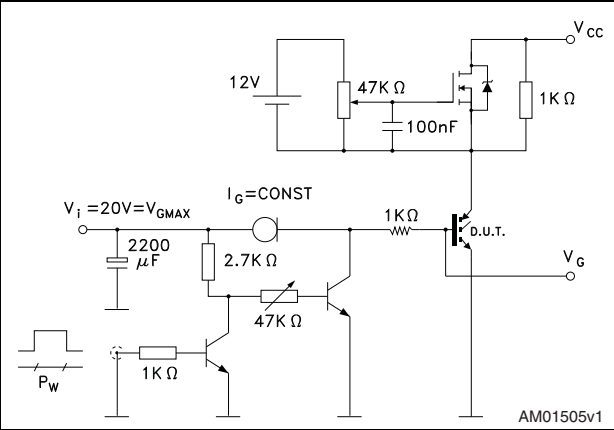


Figure 30. Switching waveform

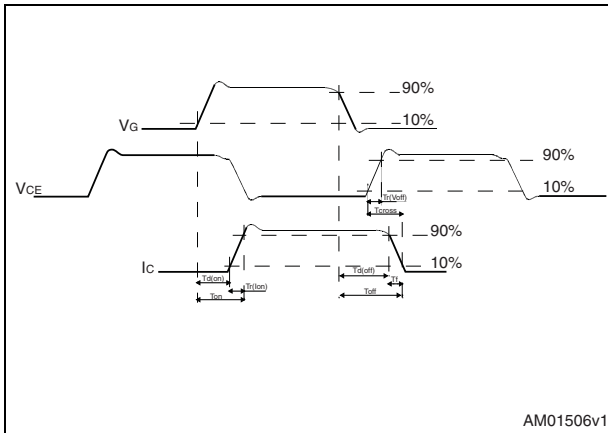
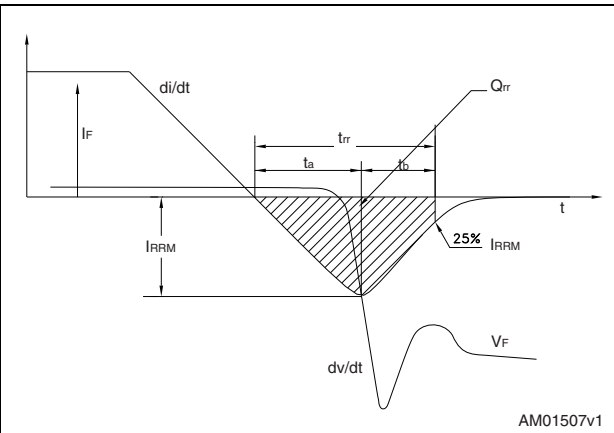


Figure 31. Diode recovery time waveform



## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

**Table 8. D<sup>2</sup>PAK (TO-263) mechanical data**

| Dim. | mm   |      |       |
|------|------|------|-------|
|      | Min. | Typ. | Max.  |
| A    | 4.40 |      | 4.60  |
| A1   | 0.03 |      | 0.23  |
| b    | 0.70 |      | 0.93  |
| b2   | 1.14 |      | 1.70  |
| c    | 0.45 |      | 0.60  |
| c2   | 1.23 |      | 1.36  |
| D    | 8.95 |      | 9.35  |
| D1   | 7.50 |      |       |
| E    | 10   |      | 10.40 |
| E1   | 8.50 |      |       |
| e    |      | 2.54 |       |
| e1   | 4.88 |      | 5.28  |
| H    | 15   |      | 15.85 |
| J1   | 2.49 |      | 2.69  |
| L    | 2.29 |      | 2.79  |
| L1   | 1.27 |      | 1.40  |
| L2   | 1.30 |      | 1.75  |
| R    |      | 0.4  |       |
| V2   | 0°   |      | 8°    |

Figure 32. D<sup>2</sup>PAK (TO-263) drawing

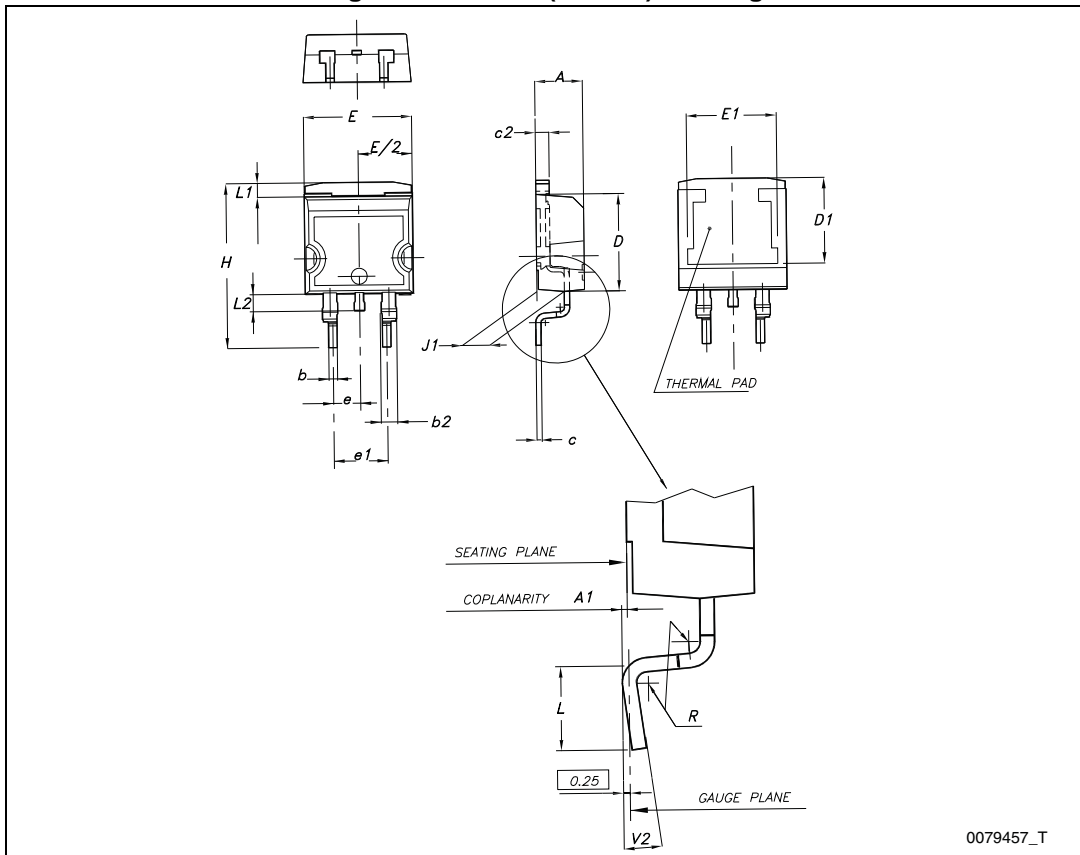
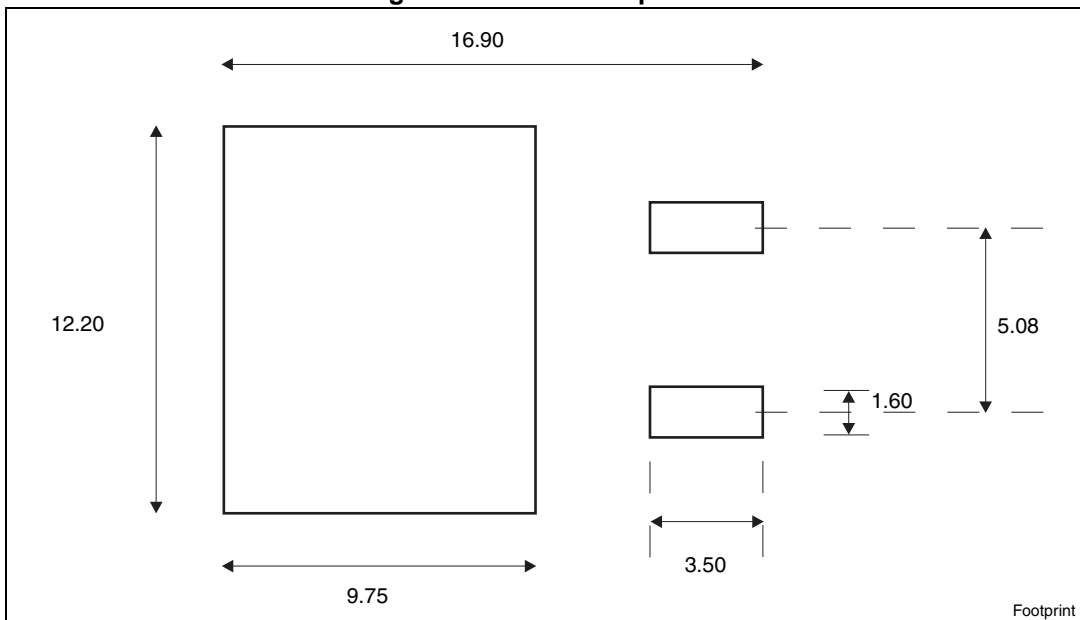


Figure 33. D<sup>2</sup>PAK footprint<sup>(a)</sup>

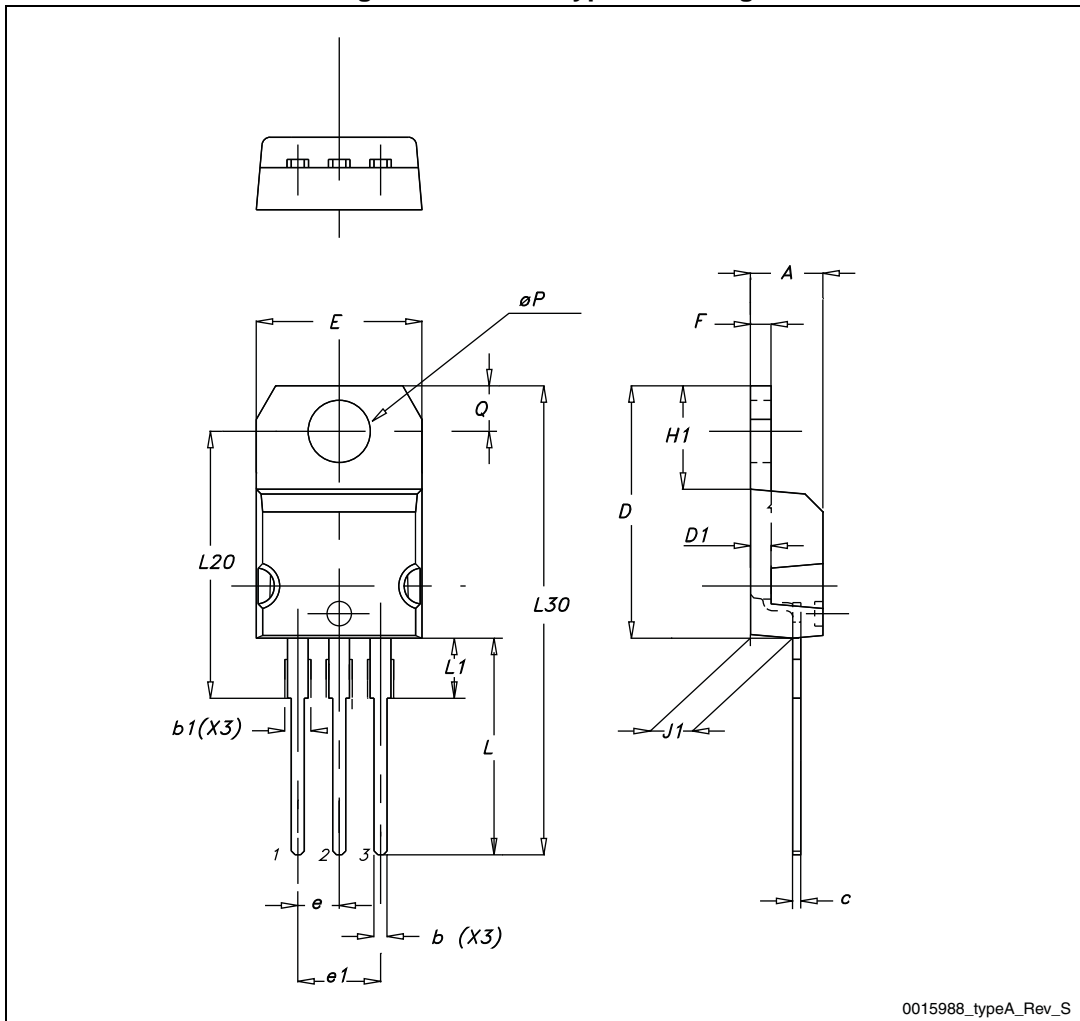


a. All dimensions are in millimeters

Table 9. TO-220 type A mechanical data

| Dim. | mm    |       |       |
|------|-------|-------|-------|
|      | Min.  | Typ.  | Max.  |
| A    | 4.40  |       | 4.60  |
| b    | 0.61  |       | 0.88  |
| b1   | 1.14  |       | 1.70  |
| c    | 0.48  |       | 0.70  |
| D    | 15.25 |       | 15.75 |
| D1   |       | 1.27  |       |
| E    | 10    |       | 10.40 |
| e    | 2.40  |       | 2.70  |
| e1   | 4.95  |       | 5.15  |
| F    | 1.23  |       | 1.32  |
| H1   | 6.20  |       | 6.60  |
| J1   | 2.40  |       | 2.72  |
| L    | 13    |       | 14    |
| L1   | 3.50  |       | 3.93  |
| L20  |       | 16.40 |       |
| L30  |       | 28.90 |       |
| ØP   | 3.75  |       | 3.85  |
| Q    | 2.65  |       | 2.95  |

Figure 34. TO-220 type A drawing



0015988\_typeA\_Rev\_S

Table 10. TO-247 mechanical data

| Dim. | mm.   |       |       |
|------|-------|-------|-------|
|      | Min.  | Typ.  | Max.  |
| A    | 4.85  |       | 5.15  |
| A1   | 2.20  |       | 2.60  |
| b    | 1.0   |       | 1.40  |
| b1   | 2.0   |       | 2.40  |
| b2   | 3.0   |       | 3.40  |
| c    | 0.40  |       | 0.80  |
| D    | 19.85 |       | 20.15 |
| E    | 15.45 |       | 15.75 |
| e    | 5.30  | 5.45  | 5.60  |
| L    | 14.20 |       | 14.80 |
| L1   | 3.70  |       | 4.30  |
| L2   |       | 18.50 |       |
| ØP   | 3.55  |       | 3.65  |
| ØR   | 4.50  |       | 5.50  |
| S    | 5.30  | 5.50  | 5.70  |

Figure 35. TO-247 drawing

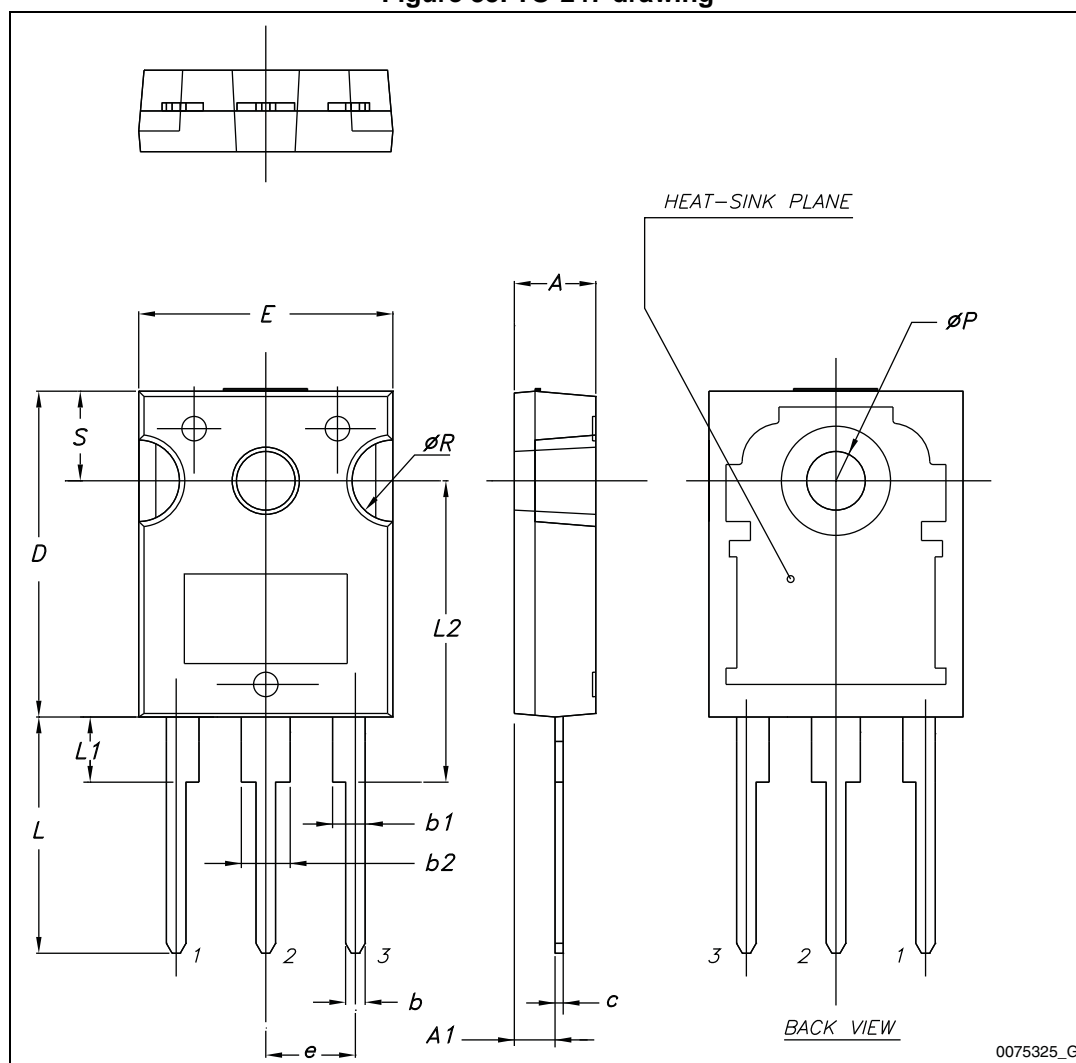
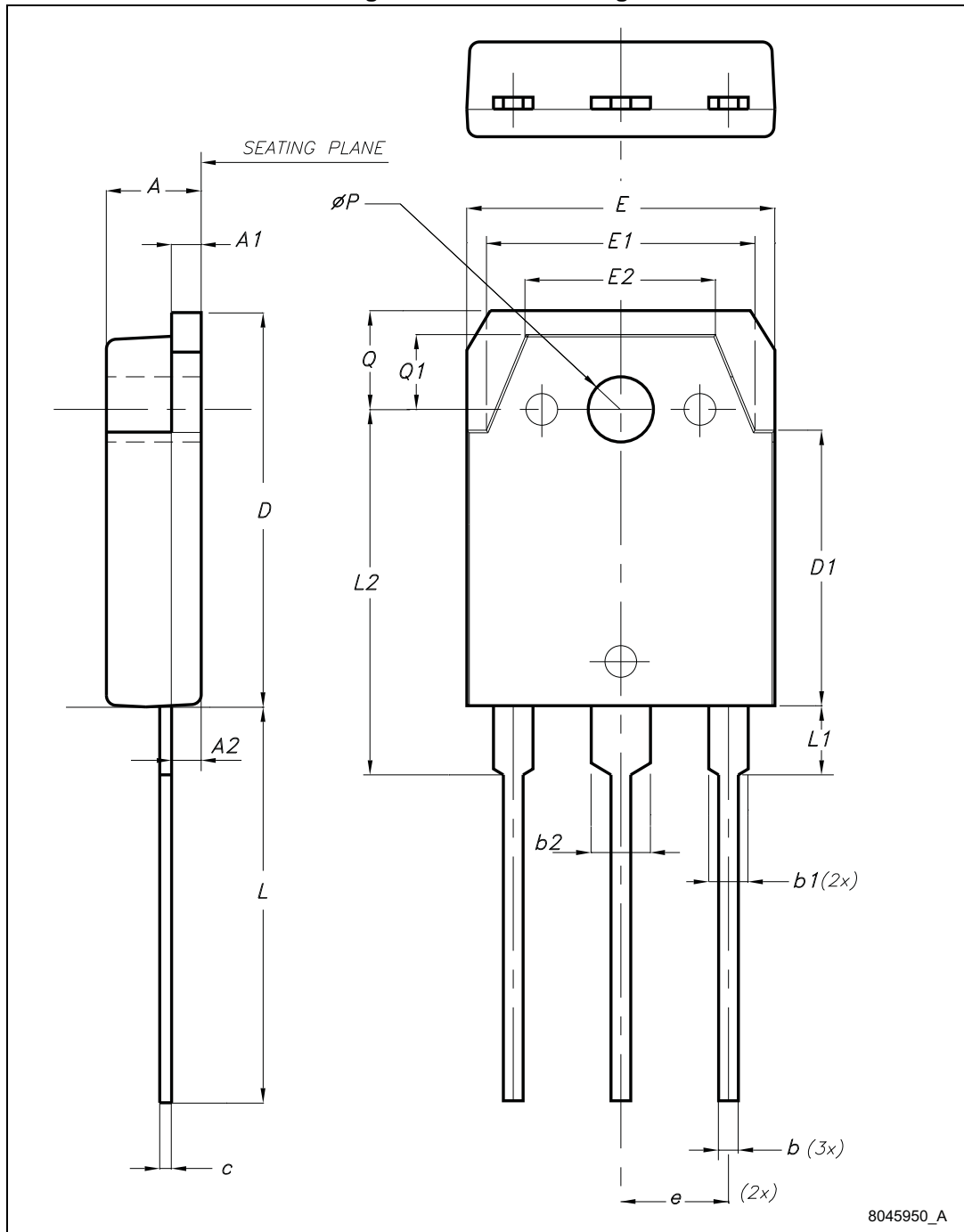




Table 11. TO-3P mechanical data

| Dim. | mm    |       |       |
|------|-------|-------|-------|
|      | Min.  | Typ.  | Max.  |
| A    | 4.60  |       | 5     |
| A1   | 1.45  | 1.50  | 1.65  |
| A2   | 1.20  | 1.40  | 1.60  |
| b    | 0.80  | 1     | 1.20  |
| b1   | 1.80  |       | 2.20  |
| b2   | 2.80  |       | 3.20  |
| c    | 0.55  | 0.60  | 0.75  |
| D    | 19.70 | 19.90 | 20.10 |
| D1   |       | 13.90 |       |
| E    | 15.40 |       | 15.80 |
| E1   |       | 13.60 |       |
| E2   |       | 9.60  |       |
| e    | 5.15  | 5.45  | 5.75  |
| L    | 19.50 | 20    | 20.50 |
| L1   |       | 3.50  |       |
| L2   | 18.20 | 18.40 | 18.60 |
| øP   | 3.10  |       | 3.30  |
| Q    |       | 5     |       |
| Q1   |       | 3.80  |       |

Figure 36. TO-3P drawing



## 5 Packaging mechanical data

Table 12. D<sup>2</sup>PAK (TO-263) tape and reel mechanical data

| Tape |      |      | Reel |          |      |
|------|------|------|------|----------|------|
| Dim. | mm   |      | Dim. | mm       |      |
|      | Min. | Max. |      | Min.     | Max. |
| A0   | 10.5 | 10.7 | A    |          | 330  |
| B0   | 15.7 | 15.9 | B    | 1.5      |      |
| D    | 1.5  | 1.6  | C    | 12.8     | 13.2 |
| D1   | 1.59 | 1.61 | D    | 20.2     |      |
| E    | 1.65 | 1.85 | G    | 24.4     | 26.4 |
| F    | 11.4 | 11.6 | N    | 100      |      |
| K0   | 4.8  | 5.0  | T    |          | 30.4 |
| P0   | 3.9  | 4.1  |      |          |      |
| P1   | 11.9 | 12.1 |      | Base qty | 1000 |
| P2   | 1.9  | 2.1  |      | Bulk qty | 1000 |
| R    | 50   |      |      |          |      |
| T    | 0.25 | 0.35 |      |          |      |
| W    | 23.7 | 24.3 |      |          |      |

Figure 37. Tape

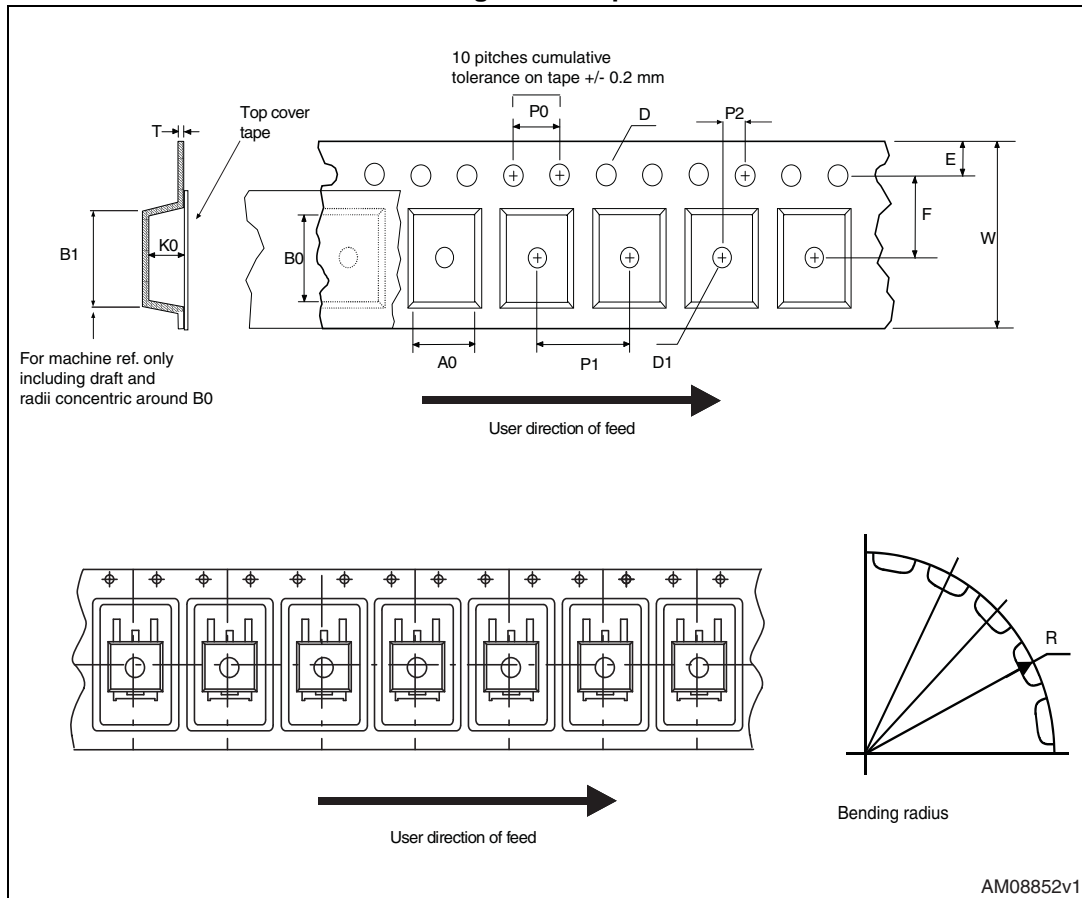
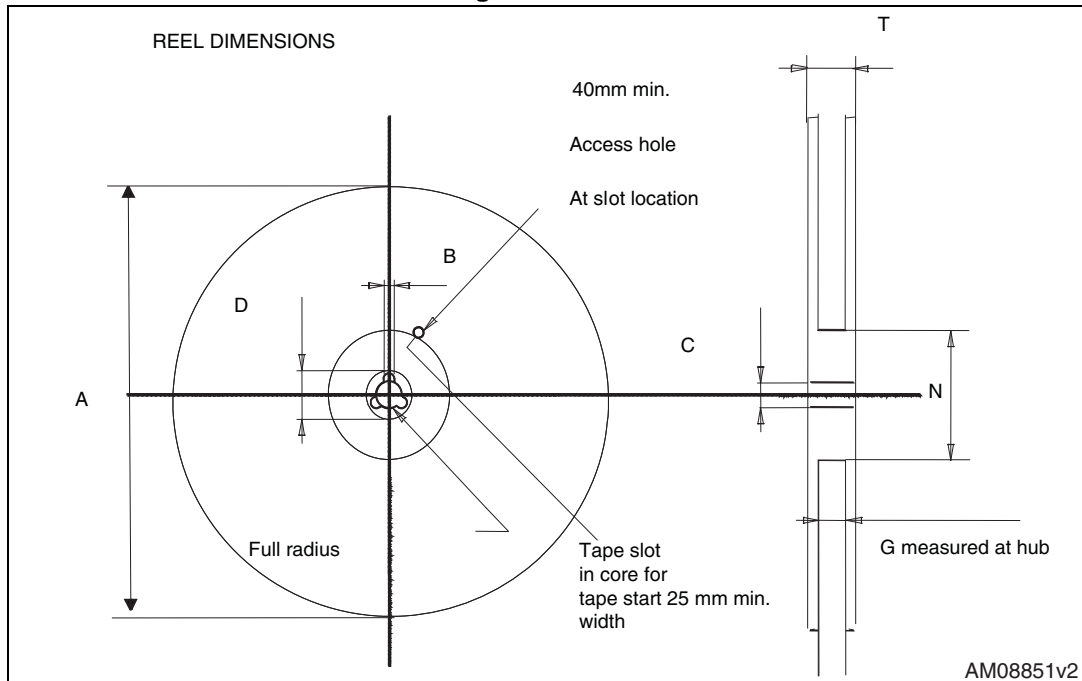


Figure 38. Reel



## 6 Revision history

Table 13. Document revision history

| Date        | Revision | Changes  |
|-------------|----------|--|
| 14-Mar-2013 | 1        | Initial release.   |
| 03-May-2013 | 2        | Added: <a href="#">Section 2.1: Electrical characteristics (curves)</a>                                |
| 04-Jun-2013 | 3        | Added minimum and maximum values for $V_{GE(th)}$ in <a href="#">Table 4: Static characteristics</a> . |

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